Vishay Semiconductors

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Hyperfast Rectifier, 30 A FRED Pt[®] G5



PRIMARY CHARACTERISTICS								
I _{F(AV)}	30 A							
V _R	1200 V							
V _F at I _F at 125 °C	1.7 V							
t _{rr}	32 ns							
T _J max.	175 °C							
Package	D ² PAK 2L (TO-263AB 2L)							
Circuit configuration	Single							

FEATURES

- Hyperfast and optimized Q_{rr}
- Best in class forward voltage drop and switching RoHS losses trade off COMPLIANT HALOGEN
- · Optimized for high speed operation
- 175 °C maximum operating junction temperature
- Polyimide passivation
- Meets MSL level, per J-Std-020, LF maximum peak of 245 °C
- AEC-Q101 gualified meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

Featuring a unique combination of low conduction and switching losses, this rectifier is the right choice for high frequency converters, both soft switched / resonant.

Specifically designed to improve efficiency of PFC and output rectification stages of EV / HEV battery charging stations, booster stage of solar inverters and UPS applications, these devices are perfectly matched to operate with MOSFETs or high speed IGBTs.

MECHANICAL DATA

Case: D²PAK 2L (TO-263AB 2L)

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS										
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS						
Repetitive peak reverse voltage	V _{RRM}		1200	V						
Average rectified forward current	I _{F(AV)}	T _C = 96 °C, D = 0.50	30							
Non-repetitive peak surge current	I _{FSM}	$T_C = 96 \ ^{\circ}C$, $t_p = 10 \ ms$, sine wave	240	А						
Repetitive peak forward current	I _{FRM}	T _C = 45 °C, D = 0.50, f = 20 kHz	60							
Operating junction and storage temperature	T _J , T _{Stg}		-55 to +175	°C						

ELECTRICAL SPECIFICATIONS ($T_J = 25$ °C unless otherwise specified)										
PARAMETER	MIN.	TYP.	MAX.	UNITS						
Breakdown voltage, blocking voltage	V_{BR}, V_{R}	I _R = 100 μA	1200	-	-					
Forward voltage	VF	I _F = 30 A	-	1.9	2.5	V				
	v _F	I _F = 30 A, T _J = 125 °C	-	1.7	-					
Povorso loakago ourront	I_	V _R = V _R rated	-	-	50	μA				
Reverse leakage current	IR	$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	-	500	μΑ				
Junction capacitance	CT	V _R = 200 V	-	17	-	pF				
Series inductance	L _S	Measured to lead 5 mm from package body	-	8	-	nH				

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VS-E5TH3012S2LHM3



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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25 \text{ °C}$ unless otherwise specified)											
PARAMETER	SYMBOL	TEST C	ONDITIONS	MIN.	TYP.	MAX.	UNITS				
		I _F = 1.0 A, dI _F /dt	= 100 A/ μ s, V _R = 30 V	-	32	-					
Reverse recovery time	t _{rr}	T _J = 25 °C		-	113	-	ns				
		T _J = 125 °C		-	175	-					
Peak recovery current		T _J = 25 °C	I _F = 20 A dI _F /dt = 600 A/μs	-	17	-	A				
	I _{RRM}	T _J = 125 °C	$V_{\rm R} = 400 \text{ V}$	-	24	-					
Reverse recovery charge	0	T _J = 25 °C		-	850	-	nC				
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	2150	-					
Powerse receiver time	+	T _J = 25 °C		-	85	-	- ns				
Reverse recovery time	t _{rr}	T _J = 125 °C		-	132	-					
Pool room ourront		T _J = 25 °C	I _F = 30 A dI _F /dt = 1000 A/μs	-	30	-	- A				
Peak recovery current	I _{RRM}	T _J = 125 °C	$V_{\rm B} = 800 \text{ V}$	-	43	-					
Powerse receivery charge	0	T _J = 25 °C		-	1350	-					
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	3215	-	nC				

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Thermal resistance, junction-to-case	R _{thJC}		-	-	1.1	°C/W				
Weight			-	2.0	-	g				
Weight			-	0.07	-	oz.				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C				
Marking device		Case style D ² PAK 2L (TO-263AB 2L)	E5TH3012SH							



100 I_F - Instantaneous Forward Current (A) 10 T_J = 175 °C 125 °C = 1 = 25 °C 0.1 0 0.5 1.0 1.5 2.0 2.5 3.0 V_F - Forward Voltage Drop (V)

Fig. 1 - Typical Forward Voltage Drop Characteristics

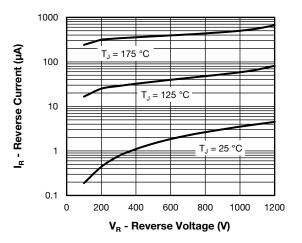


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

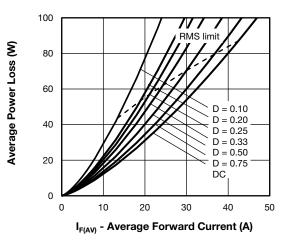


Fig. 5 - Forward Power Loss Characteristics

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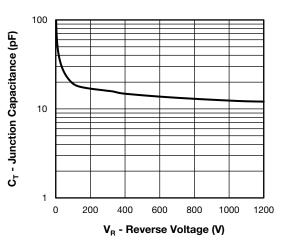
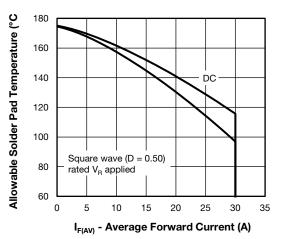
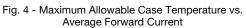


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage





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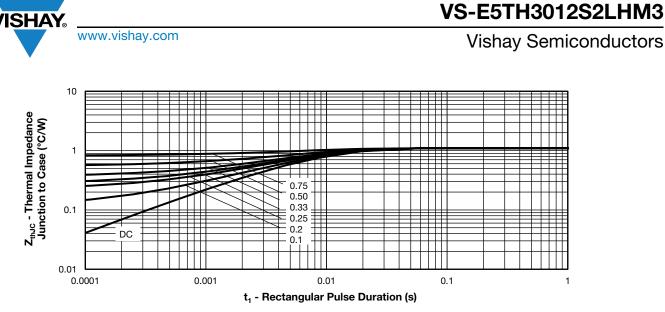


Fig. 6 - Thermal Impedance ZthJC Characteristics

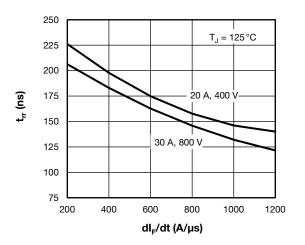
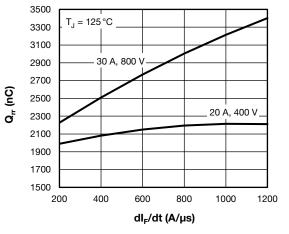


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt





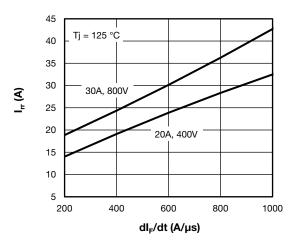


Fig. 9 - Typical Recovery Current vs. dI_F/dt





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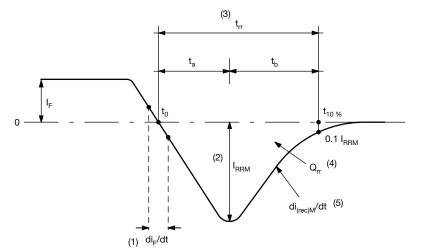


Fig. 10 - Reverse Recovery Waveform and Definitions

Notes

- ⁽¹⁾ di_F/dt rate of change of current through zero crossing
- $^{(2)}\ \ I_{RRM}$ peak reverse recovery current
- ⁽³⁾ t_{rr} reverse recovery time measured from t_0 , crossing point of negative going I_F, to point $t_{10\%}$, 0.1 I_{RRM}
- $^{(4)}$ Q_{rr} area under curve defined by t_0 and $t_{10\ \%}$

$$Q_{rr} = \int_{t_0}^{t_{10\%}} I(t) dt$$

 $^{(5)}$ di_(rec)M/dt - peak rate of change of current during t_b portion of t_{rr}

ORDERING INFORMATION TABLE

Device code	VS-	E	5	т	н	30	12	S2	L	н	М3
	1	2	3	4	5	6	7	8	9	(10)	(11)
	1 ·	- Visl	nay Sem	niconduo	ctors pr	oduct					
	2	- E=	single c	liode							
	3	- 5 =	FRED g	eneratio	on 5						
	4		kage:								
			D ² PAK		<i>,</i> .	age					
		- H=	hyperfa	st recov	very						
	6	- Cur	rent rati	ng (30 =	= 30 A)						
	7 -	- Vol	tage rati	ng (12 =	= 1200 \	/)					
	8	- S2	= true 2	pin D ² F	PAK						
	9	- Noi	ne = tub	e (50 pi	eces)						
		 L = tape and reel (left oriented, for D²PAK package) 									
	If needed different orientation/packaging, please contact factory									,	
	10	10 - H = AEC-Q101 qualified									
	11 ·	- Env	vironmer	ntal digit	t:						
		M3	= halog	en-free,	RoHS-	complia	ant, and	termina	tion lea	d (Pb)-f	ree



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ORDERING INFORMATION (Example)										
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION							
VS-E5TH3012S2LHM3	800	800	13" diameter reel							
LINKS TO RELATED DOCUME	INTS									
Dimensions		www.vishay.co	om/doc?96683							
Part marking information			om/doc?96693							
Packaging information		www.vishay.com/doc?95032								

Outline Dimensions

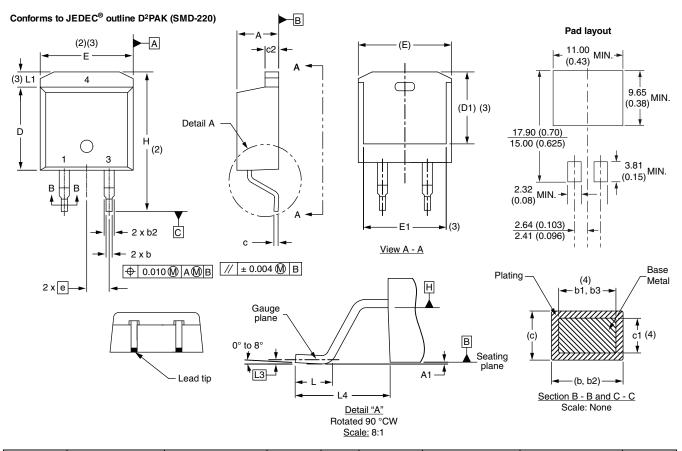


2L-D²PAK

DIMENSIONS in millimeters and inches

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SHAY



SYMBOL	MILLIMETERS		INC	HES	NOTES	NOTES		MILLIM	ETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
А	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			Е	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L3	0.25 BSC		0.010	BSC	
c2	1.14	1.65	0.045	0.065			L4	4.78	5.28	0.188	0.208	
D	8.51	9.65	0.335	0.380	2							

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

⁽²⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
 ⁽²⁾ The outmost extremes of the plastic body

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inch

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

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